

PS2535-1, PS2535L-1**HIGH COLLECTOR TO EMITTER VOLTAGE
HIGH ISOLATION VOLTAGE
MULTI PHOTOCOUPLER SERIES**

—NEPOC Series—

DESCRIPTION

The PS2535-1 and PS2535L-1 are optically coupled isolators containing a GaAs light emitting diode and an NPN silicon darlington connected phototransistor.

A high withstanding voltage between the I/O, the high voltage between the collector and emitter of the transistor, and darlington transistor output enables low-current input.

The PS2535-1 is in a plastic DIP (Dual In-line Package) and the PS2535L-1 is lead bending type (Gull-wing) for surface mount.

FEATURES

- High collector to emitter voltage ($V_{CEO} = 350\text{ V}$)
- High isolation voltage ($BV = 5\,000\text{ V r.m.s.}$)
- High current transfer ratio ($CTR = 1\,500\% \text{ TYP.}$)
- Ordering number of taping product: PS2535L-1-E3, E4, F3, F4

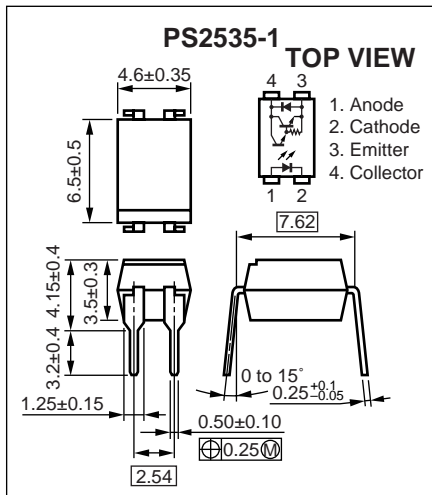
APPLICATIONS

- Telephone, Exchange equipment
- FAX/MODEM

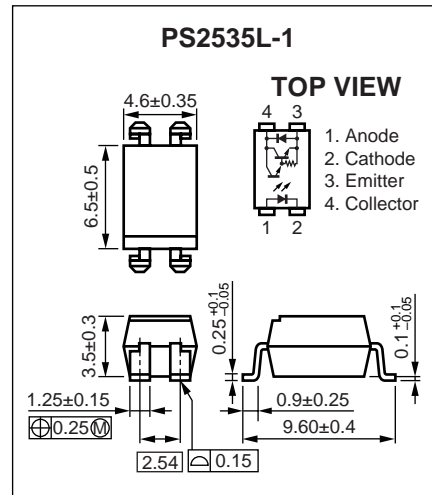
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★ PACKAGE DIMENSIONS (Unit : mm)

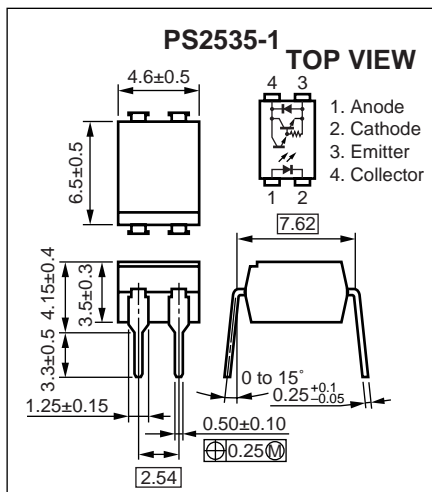
DIP Type (New package)



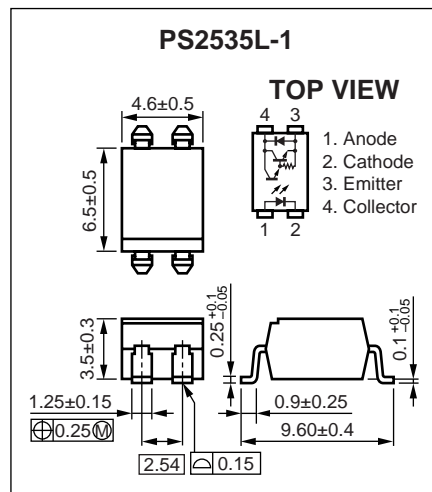
Lead Bending Type (New package)



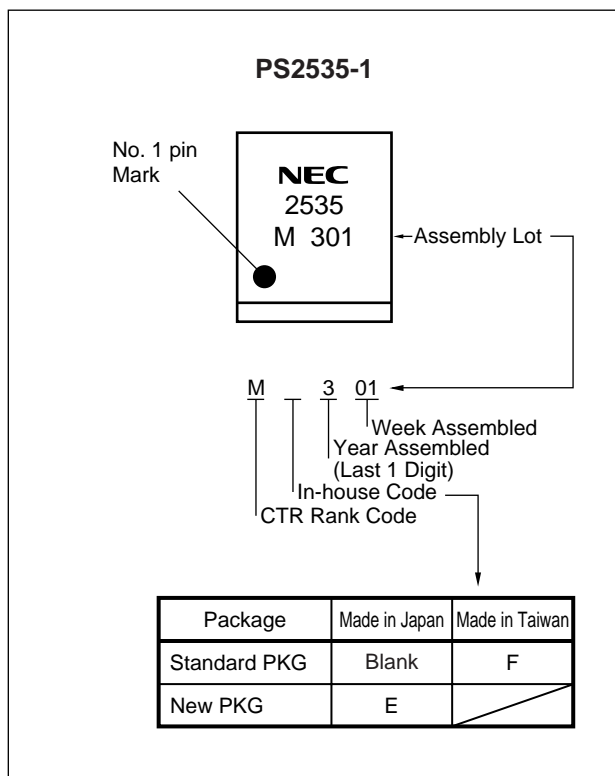
DIP Type



Lead Bending Type



★ MARKING EXAMPLE



★ ORDERING INFORMATION

Part Number	Package	Packing Style	Application Part Number ^{*1}
PS2535-1	4-pin DIP	Magazine case 100 pcs	PS2535-1
PS2535L-1			
PS2535L-1-E3		Embossed Tape 1 000 pcs/reel	
PS2535L-1-E4			
PS2535L-1-F3		Embossed Tape 2 000 pcs/reel	
PS2535L-1-F4			

*1 For the application of the Safety Standard, following part number should be used.

★ ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Diode	Forward Current (DC)	I _F	50	mA
	Reverse Voltage	V _R	6	V
	Power Dissipation Derating	ΔP _D /°C	0.7	mW/°C
	Power Dissipation	P _D	70	mW
	Peak Forward Current ^{*1}	I _{FP}	0.5	A
Transistor	Collector to Emitter Voltage	V _{CEO}	350	V
	Emitter to Collector Voltage	V _{ECO}	0.3	V
	Collector Current	I _C	120	mA
	Power Dissipation Derating	ΔP _C /°C	2.0	mW/°C
	Power Dissipation	P _C	200	mW
Isolation Voltage ^{*2}		BV	5 000	Vr.m.s.
Operating Ambient Temperature		T _A	−55 to +100	°C
Storage Temperature		T _{stg}	−55 to +150	°C

*1 PW = 100 μs, Duty Cycle = 1 %

*2 AC voltage for 1 minute at T_A = 25 °C, RH = 60 % between input and output

ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$)

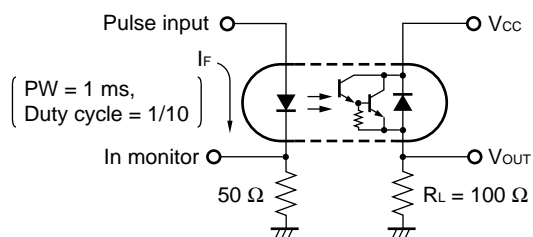
Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
★ Diode	Forward Voltage	V_F	$I_F = 10\text{ mA}$		1.2	1.4	V
	Reverse Current	I_R	$V_R = 5\text{ V}$			5	μA
	Terminal Capacitance	C_t	$V = 0\text{ V}, f = 1.0\text{ MHz}$		15		pF
★ Transistor	Collector to Emitter Dark Current	I_{CEO}	$V_{CE} = 350\text{ V}, I_F = 0\text{ mA}$			400	nA
Coupled	Current Transfer Ratio (I_C/I_F) ^{*1}	CTR	$I_F = 1\text{ mA}, V_{CE} = 2\text{ V}$	400	1 500	5 500	%
	Collector Saturation Voltage	$V_{CE(sat)}$	$I_F = 1\text{ mA}, I_C = 2\text{ mA}$			1.0	V
	Isolation Resistance	R_{I-O}	$V_{I-O} = 1.0\text{ kV}_{DC}$	10^{11}			Ω
	Isolation Capacitance	C_{I-O}	$V = 0\text{ V}, f = 1.0\text{ MHz}$		0.6		pF
	Rise Time ^{*2}	t_r	$V_{CC} = 5\text{ V}, I_C = 10\text{ mA}, R_L = 100\text{ }\Omega$		18		μs
	Fall Time ^{*2}	t_f			5		

*1 CTR rank

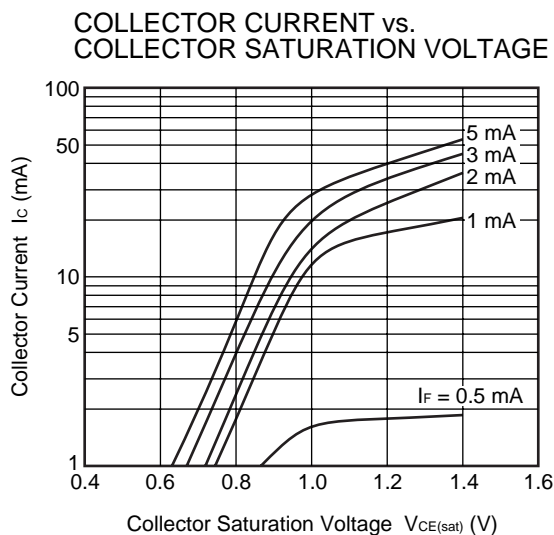
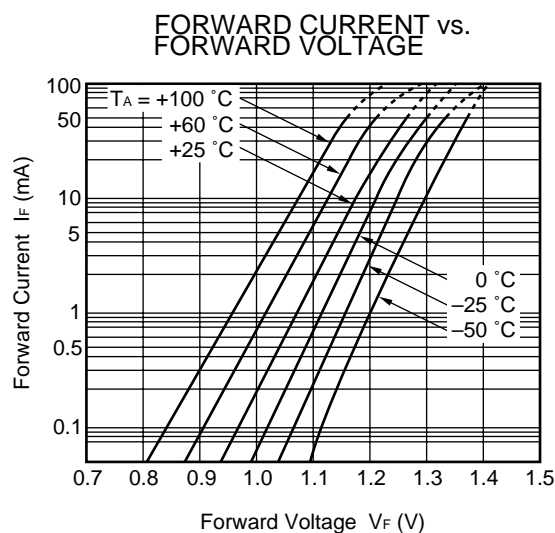
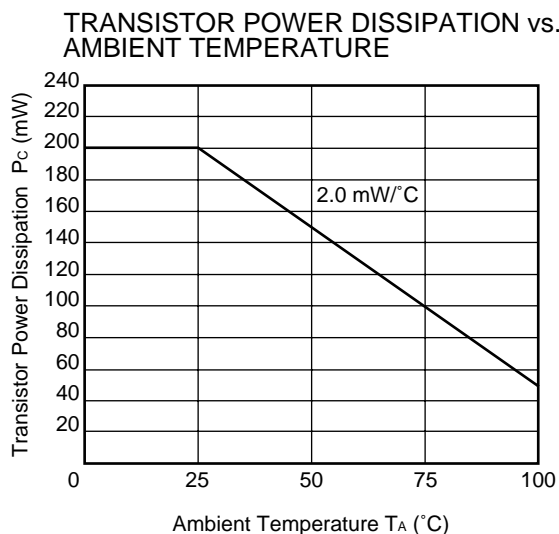
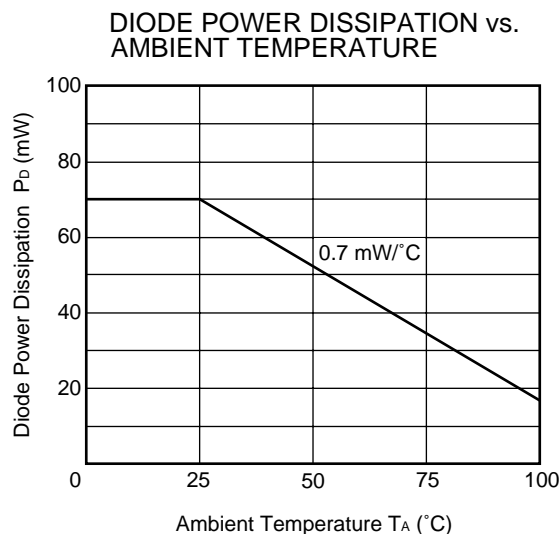
N : 400 to 5 500 (%)

L : 1 500 to 5 500 (%)

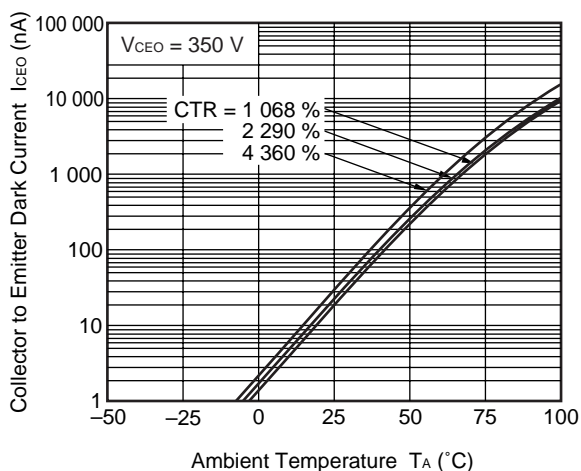
*2 Test circuit for switching time



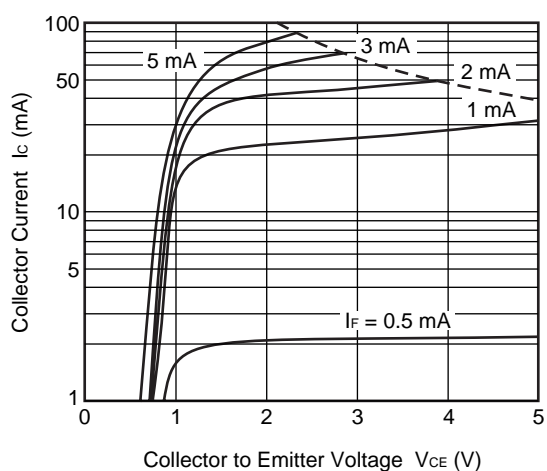
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)



★ **COLLECTOR TO EMITTER DARK CURRENT vs. AMBIENT TEMPERATURE**

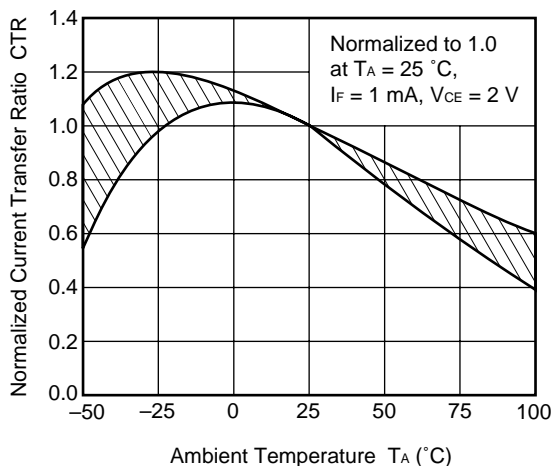


COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE

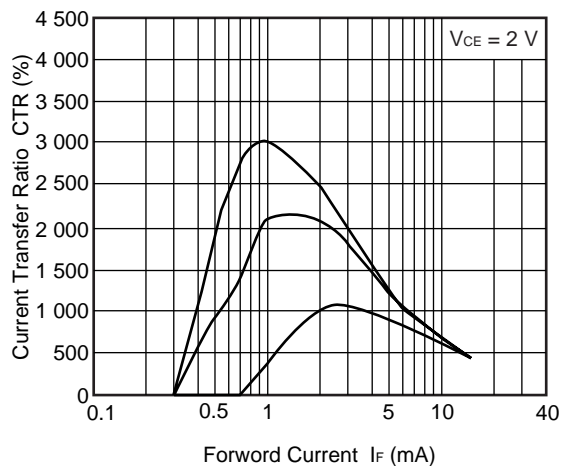


Remark The graphs indicate nominal characteristics.

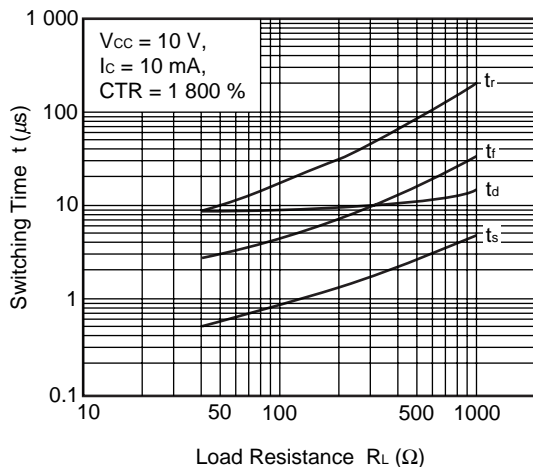
NORMALIZED CURRENT TRANSFER RATIO vs. AMBIENT TEMPERATURE



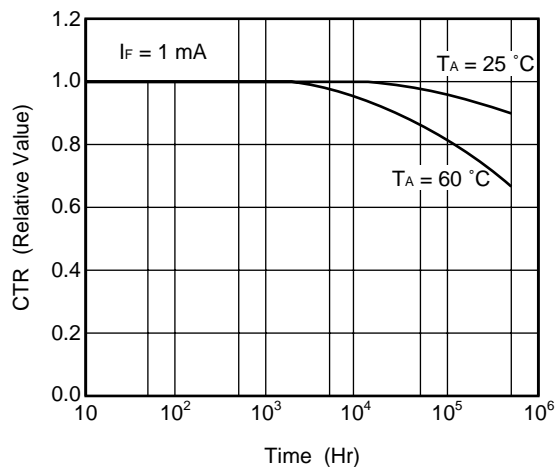
CURRENT TRANSFER RATIO vs. FORWARD CURRENT



SWITCHING TIME vs. LOAD RESISTANCE



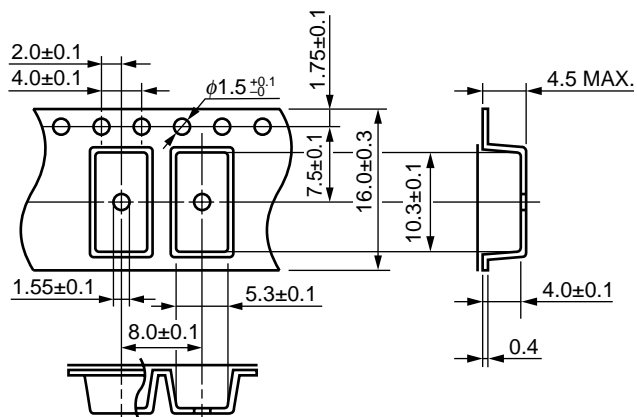
LONG TERM CTR DEGRADATION



Remark The graphs indicate nominal characteristics.

★ TAPING SPECIFICATIONS (in millimeters)

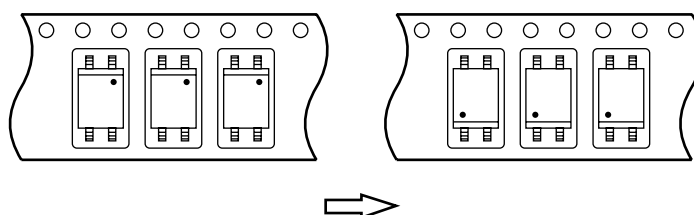
Outline and Dimensions (Tape)



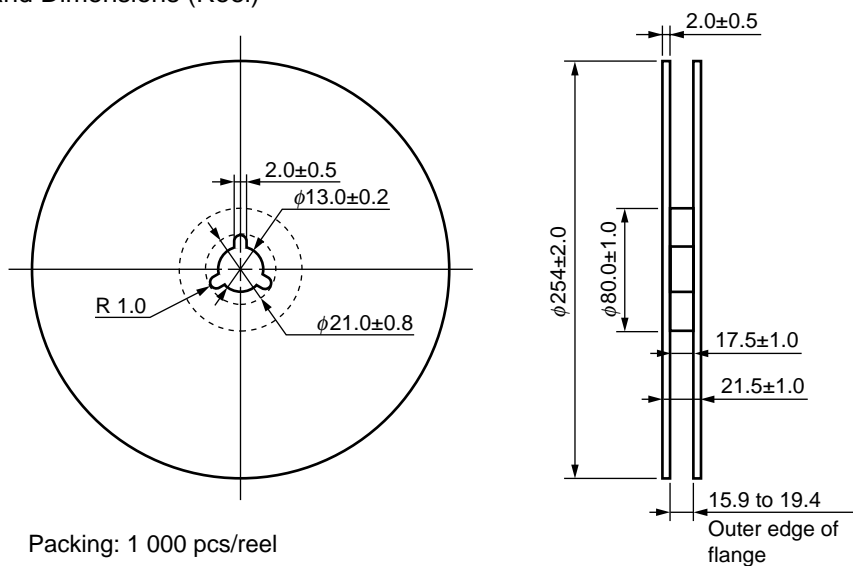
Tape Direction

PS2535L-1-E3

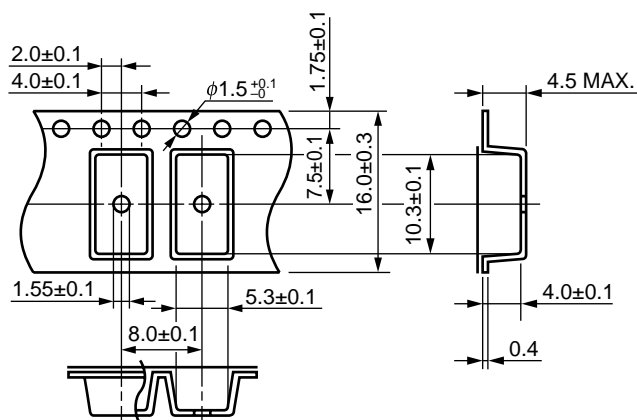
PS2535L-1-E4



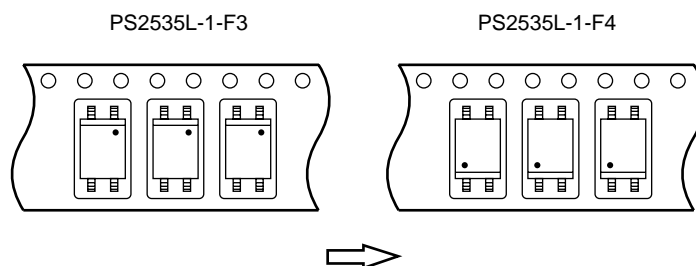
Outline and Dimensions (Reel)



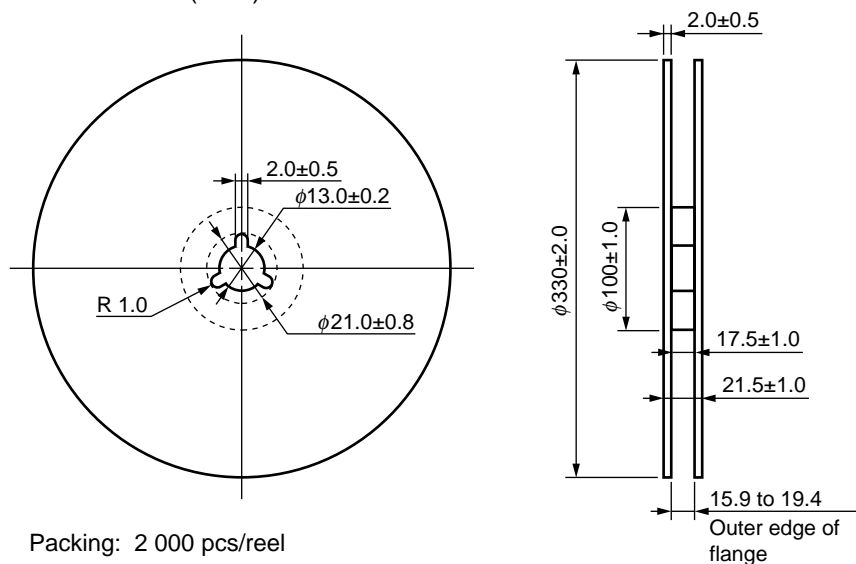
Outline and Dimensions (Tape)



Tape Direction



Outline and Dimensions (Reel)



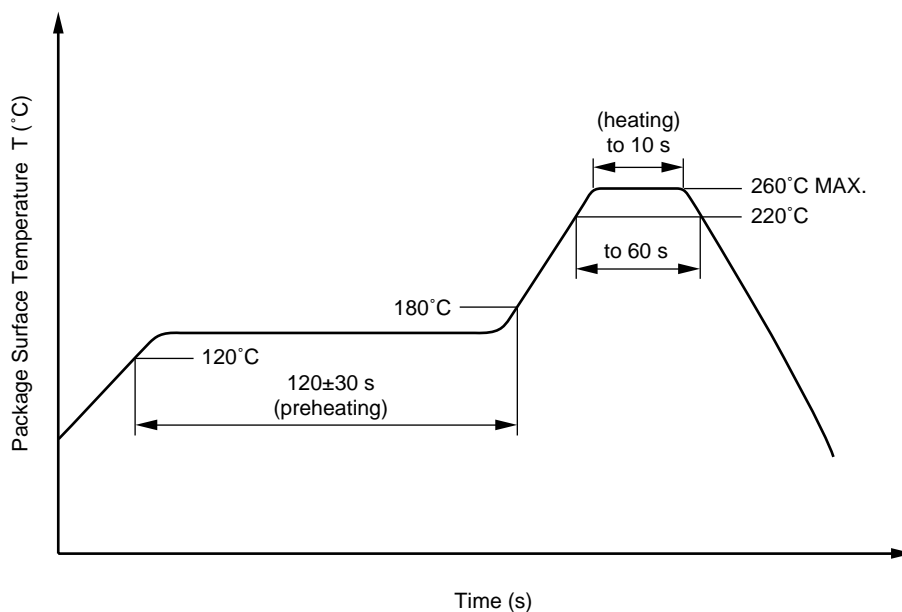
★ NOTES ON HANDLING

1. Recommended soldering conditions

(1) Infrared reflow soldering

- Peak reflow temperature 260°C or below (package surface temperature)
- Time of peak reflow temperature 10 seconds or less
- Time of temperature higher than 220°C 60 seconds or less
- Time to preheat temperature from 120 to 180°C 120±30 s
- Number of reflows Three
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

Recommended Temperature Profile of Infrared Reflow



(2) Wave soldering

- Temperature 260°C or below (molten solder temperature)
- Time 10 seconds or less
- Preheating conditions 120°C or below (package surface temperature)
- Number of times One (Allowed to be dipped in solder including plastic mold portion.)
- Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

(3) Cautions

- Fluxes
Avoid removing the residual flux with freon-based and chlorine-based cleaning solvent.

2. Cautions regarding noise

Be aware that when voltage is applied suddenly between the photocoupler's input and output or between collector-emitters at startup, the output side may enter the on state, even if the voltage is within the absolute maximum ratings.

★ USAGE CAUTIONS

1. Protect against static electricity when handling.
2. Avoid storage at a high temperature and high humidity.

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M8E 00.4-0110

Caution	GaAs Products	<p>This product uses gallium arsenide (GaAs). GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.</p> <ul style="list-style-type: none"> • Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below. <ol style="list-style-type: none"> 1. Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials. 2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal. • Do not burn, destroy, cut, crush, or chemically dissolve the product. • Do not lick the product or in any way allow it to enter the mouth.
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► For further information, please contact

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